

Byong-Guk Park

List of Publications by Year in descending order

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65

papers

2,806

citations

331670

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175258

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72

all docs

72

docs citations

72

times ranked

3305

citing authors

#	ARTICLE	IF	CITATIONS
1	Reduced Spin-orbit Torque Switching Current by Voltage-controlled Easy-Easy' Cone States. <i>Advanced Functional Materials</i> , 2022, 32, 2107944.	14.9	2
2	Thickness dependence of spin-orbit torques in Pt/Co structures on epitaxial substrates. <i>APL Materials</i> , 2022, 10, .	5.1	5
3	SOT-MRAM Digital PIM Architecture With Extended Parallelism in Matrix Multiplication. <i>IEEE Transactions on Computers</i> , 2022, 71, 2816-2828.	3.4	8
4	Efficient spin-orbit torque in magnetic trilayers using all three polarizations of a spin current. <i>Nature Electronics</i> , 2022, 5, 217-223.	26.0	28
5	Voltage-driven gigahertz frequency tuning of spin Hall nano-oscillators. <i>Nature Communications</i> , 2022, 13, .	12.8	14
6	Anisotropic Spin-Orbit Torque through Crystal-Orientation Engineering in Epitaxial $\langle mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="block">\text{Pt}$. <i>Physical Review Applied</i> , 2021, 15, .	3.8	13
7	Magnetization switching through symmetry. <i>Nature Nanotechnology</i> , 2021, 16, 227-228.	31.5	6
8	Magnetic Anisotropy and Damping Constant of Ferrimagnetic GdCo Alloy near Compensation Point. <i>Materials</i> , 2021, 14, 2604.	2.9	10
9	Morphology-dependent spin Seebeck effect in yttrium iron garnet thin films prepared by metal-organic decomposition. <i>Ceramics International</i> , 2021, 47, 16770-16775.	4.8	11
10	Unconventional Hall effect in metal/semiconductor hybrid spintronic devices. <i>Applied Physics Letters</i> , 2021, 119, 112401.	3.3	1
11	Stochastic SOT device based SNN architecture for On-chip Unsupervised STDP Learning. <i>IEEE Transactions on Computers</i> , 2021, , 1-1.	3.4	7
12	Temperature dependence of intrinsic and extrinsic contributions to anisotropic magnetoresistance. <i>Scientific Reports</i> , 2021, 11, 20884.	3.3	10
13	Efficient conversion of orbital Hall current to spin current for spin-orbit torque switching. <i>Communications Physics</i> , 2021, 4, .	5.3	65
14	Current-induced manipulation of exchange bias in IrMn/NiFe bilayer structures. <i>Nature Communications</i> , 2021, 12, 6420.	12.8	24
15	Unidirectional spin Hall magnetoresistance in epitaxial Cr/Fe bilayer from electron-magnon scattering. <i>Communications Physics</i> , 2021, 4, .	5.3	7
16	Enhanced spin-orbit torque in Ni ₈₁ Fe ₁₉ /Pt bilayer with NdNiO ₃ contact. <i>Applied Physics Letters</i> , 2021, 119, .	3.3	2
17	Orbital torque in magnetic bilayers. <i>Nature Communications</i> , 2021, 12, 6710.	12.8	69
18	Electric-field control of field-free spin-orbit torque switching via laterally modulated Rashba effect in Pt/Co/AlOx structures. <i>Nature Communications</i> , 2021, 12, 7111.	12.8	36

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19	Observation of Thermal Spin-orbit Torque in W/CoFeB/MgO Structures. <i>Nano Letters</i> , 2020, 20, 7803-7810.	9.1	7
20	Negative spin Hall magnetoresistance of normal metal/ferromagnet bilayers. <i>Nature Communications</i> , 2020, 11, 3619.	12.8	13
21	Control of electrical resistance and magnetoresistance by electric-field-driven oxygen ion migration in a single GdOx wire. <i>NPG Asia Materials</i> , 2020, 12, .	7.9	4
22	Extreme anti-reflection enhanced magneto-optic Kerr effect microscopy. <i>Nature Communications</i> , 2020, 11, 5937.	12.8	21
23	Amplification of Spin Thermoelectric Signals in Multilayer Spin Thermopiles. <i>ACS Applied Electronic Materials</i> , 2020, 2, 2906-2912.	4.3	4
24	Current-induced Spin-orbit Torques for Spintronic Applications. <i>Advanced Materials</i> , 2020, 32, e1907148.	21.0	121
25	Distinct handedness of spin wave across the compensation temperatures of ferrimagnets. <i>Nature Materials</i> , 2020, 19, 980-985.	27.5	42
26	Spin-Orbit Torque in a Perpendicularly Magnetized Ferrimagnetic $\text{Tb}_{1-x}\text{Co}_x$ Single Layer. <i>Physical Review Applied</i> , 2020, 13, .	3.8	43
27	Effects of proton and ion beam radiation on magnetic tunnel junctions. <i>Thin Solid Films</i> , 2019, 686, 137432.	1.8	12
28	Material and Thickness Investigation in Ferromagnet/Ta/CoFeB Trilayers for Enhancement of Spin-orbit Torque and Field-free Switching. <i>Advanced Electronic Materials</i> , 2019, 5, 1900598.	5.1	23
29	Underlayer dependence of electric field effect on magnetic anisotropy and its volatility in CoFeB/MgO structures. <i>Current Applied Physics</i> , 2019, 19, 50-54.	2.4	1
30	Antiferromagnetic Oscillators Driven by Spin Currents with Arbitrary Spin Polarization Directions. <i>Physical Review Applied</i> , 2019, 11, .	3.8	14
31	Spectrometer based real-time magnetic Faraday rotation spectroscopy of Bi-YIG thin films. <i>Journal of Magnetism and Magnetic Materials</i> , 2019, 482, 61-65.	2.3	7
32	Enhanced spin-orbit torque via interface engineering in Pt/CoFeB/MgO heterostructures. <i>APL Materials</i> , 2019, 7, .	5.1	48
33	Anisotropic magnetoresistance of 3d Ferromagnetic metals observed by terahertz time domain spectroscopy. , 2019, .		0
34	Largely enhanced coercivity of cobalt adjacent to straight-stripe mixed-phase bismuth ferrites. <i>Physical Review B</i> , 2018, 97, .	3.2	2
35	Spin currents and spin-orbit torques in ferromagnetic trilayers. <i>Nature Materials</i> , 2018, 17, 509-513.	27.5	337
36	Precise Determination of the Temperature Gradients in Laser-irradiated Ultrathin Magnetic Layers for the Analysis of Thermal Spin Current. <i>Scientific Reports</i> , 2018, 8, 11337.	3.3	2

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37	Complementary logic operation based on electric-field controlled spin-orbit torques. <i>Nature Electronics</i> , 2018, 1, 398-403.	26.0	100
38	Plasmon-enhanced Photodetection in Ferromagnet/Nonmagnet Spin Thermoelectric Structures. <i>Advanced Functional Materials</i> , 2018, 28, 1802936.	14.9	7
39	Enhanced tunnel magnetoresistance and electric-field effect in CoFeB/MgO/CoFeB perpendicular tunnel junctions with W underlayer. <i>Current Applied Physics</i> , 2017, 17, 962-965.	2.4	14
40	Novel Operation of a Multi-Bit SOT Memory Cell Addressed With a Single Write Line. <i>IEEE Transactions on Magnetics</i> , 2017, 53, 1-5.	2.1	3
41	Integrated arrays of air-dielectric graphene transistors as transparent active-matrix pressure sensors for wide pressure ranges. <i>Nature Communications</i> , 2017, 8, 14950.	12.8	167
42	Inertia-driven resonant excitation of a magnetic skyrmion. <i>Scientific Reports</i> , 2017, 7, 13993.	3.3	14
43	Enhanced spin-orbit torque by engineering Pt resistivity in $\text{Co}_{32}\text{Pt}_{65}$ structures. <i>Physical Review B</i> , 2017, 96, .	3.2	1
44	Observation of transverse spin Nernst magnetoresistance induced by thermal spin current in ferromagnet/non-magnet bilayers. <i>Nature Communications</i> , 2017, 8, 1400.	12.8	36
45	Spin Hall magnetoresistance in heavy-metal/metallic-ferromagnet multilayer structures. <i>Physical Review B</i> , 2017, 96, .	3.2	20
46	Contributions of Co and Fe orbitals to perpendicular magnetic anisotropy of MgO/CoFeB bilayers with Ta, W, IrMn, and Ti underlayers. <i>Applied Physics Express</i> , 2017, 10, 073006.	2.4	9
47	Hardness of AISI type 410 martensitic steels after high temperature irradiation via nanoindentation. <i>Metals and Materials International</i> , 2017, 23, 1257-1265.	3.4	9
48	Relativistic Motion of Antiferromagnetic Domain Walls Driven by Spin-Orbit Torques. , 2016, , .		0
49	Field-free switching of perpendicular magnetization through spin-orbit torque in antiferromagnet/ferromagnet/oxide structures. <i>Nature Nanotechnology</i> , 2016, 11, 878-884.	31.5	438
50	Utilization of the Antiferromagnetic IrMn Electrode in Spin Thermoelectric Devices and Their Beneficial Hybrid for Thermopiles. <i>Advanced Functional Materials</i> , 2016, 26, 5507-5514.	14.9	21
51	Electric field control of magnetic anisotropy in the easy cone state of Ta/Pt/CoFeB/MgO structures. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	23
52	Antiferromagnetic Domain Wall Motion Driven by Spin-Orbit Torques. <i>Physical Review Letters</i> , 2016, 117, 087203.	7.8	201
53	Effect of Proton Irradiation on the Magnetic Properties of Antiferromagnet/ferromagnet Structures. <i>Journal of Magnetics</i> , 2016, 21, 159-163.	0.4	3
54	Thermoelectric Signal Enhancement by Reconciling the Spin Seebeck and Anomalous Nernst Effects in Ferromagnet/Non-magnet Multilayers. <i>Scientific Reports</i> , 2015, 5, 10249.	3.3	65

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55	Magneto-optical kerr spectroscopy and interfacial perpendicular magnetic anisotropy of (Hf,Pt)/CoFeB/MgO thin films. <i>Journal of the Korean Physical Society</i> , 2015, 67, 1235-1239.	0.7	4
56	Large spin Hall magnetoresistance and its correlation to the spin-orbit torque in W/CoFeB/MgO structures. <i>Scientific Reports</i> , 2015, 5, 14668.	3.3	147
57	Large planar Hall effect in perpendicularly magnetized W/CoFeB/MgO structures. <i>Current Applied Physics</i> , 2015, 15, 902-905.	2.4	11
58	Fast current-induced motion of a transverse domain wall induced by interfacial Dzyaloshinskii-Moriya interaction. <i>Current Applied Physics</i> , 2015, 15, 1139-1142.	2.4	4
59	Magnetic resonance absorption in isolated metal/insulator/metal nanodot arrays with transmission geometry. <i>Current Applied Physics</i> , 2015, 15, 844-849.	2.4	3
60	Dependence of inverse-spin Hall effect and spin-rectified voltage on tantalum thickness in Ta/CoFeB bilayer structure. <i>Applied Physics Letters</i> , 2015, 106, 032409.	3.3	15
61	Dissipative soliton dynamics in a discrete magnetic nano-dot chain. <i>Applied Physics Letters</i> , 2014, 104, 052416.	3.3	6
62	Interfacial perpendicular magnetic anisotropy in CoFeB/MgO structure with various underlayers. <i>Journal of Applied Physics</i> , 2014, 115, .	2.5	56
63	Ferromagnetic resonance spin pumping in CoFeB with highly resistive non-magnetic electrodes. <i>Current Applied Physics</i> , 2014, 14, 1344-1348.	2.4	28
64	CuO-based sintering aids for low temperature sintering of BaFe ₁₂ O ₁₉ ceramics. <i>Journal of Asian Ceramic Societies</i> , 2013, 1, 170-177.	2.3	21
65	Spin Hall Effect Transistor. <i>Science</i> , 2010, 330, 1801-1804.	12.6	288